

## JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

# **SMAF Plastic-Encapsulate Diodes**

# **S2AF THRU S2MF** General Purpose Rectifier Diodes

#### **Features**

• I<sub>F(AV)</sub> 2A

●VRRM 50V-1000V

High surge current capability

• Polarity: Color band denotes cathode

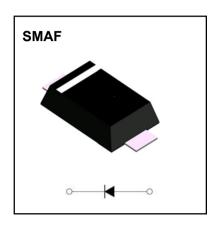
### **Applications**

Rectifier

### **Marking**

• S2X

X: From A To M



### **Limiting Values(Absolute Maximum Rating)**

<b>1</b> 4	Symbol	Unit		S2						
Item			Test Conditions	AF	BF	DF	GF	JF	KF	MF
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V <sub>RMS</sub>	V		35	70	140	280	420	560	700
Average Forward Current	I <sub>F(AV)</sub>	А	60Hz Half-sine wave , Resistance load , T <sub>L</sub> =110 ℃	2.0						
Surge(Non-repetitive)Forward Current	I <sub>FSM</sub>	А	60Hz Half-sine wave , 1 cycle,Ta=25℃	60						
Operation Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	$^{\circ}$		-55 ~ <b>+</b> 150						

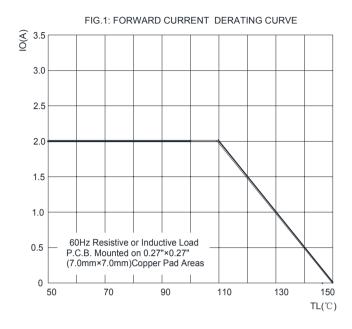
Electrical Characteristics (T=25°C Unless otherwise specified)

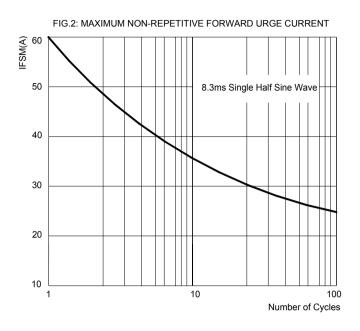
Item	Symbol	Unit	Test Condition		MAX
Peak Forward Voltage	V <sub>F</sub>	٧	I <sub>F</sub> =2.0A		1.0
Peak Reverse Current	I <sub>RRM1</sub>	μA	V <sub>RM</sub> =V <sub>RRM</sub>	T <sub>a</sub> =25℃	5
	I <sub>RRM2</sub>			T <sub>a</sub> =125℃	50
hermal $R_{ heta_{ ext{J-A}}}$		°C/W	Between junction and ambient		55
Resistance(Typical)	$R_{ heta J ext{-}L}$	CTVV	Between junction and terminal		16

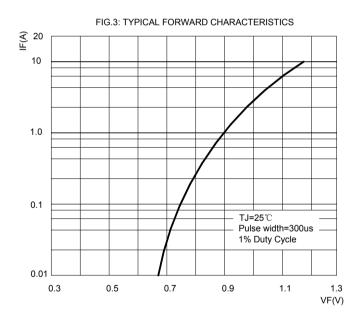
#### Notes:

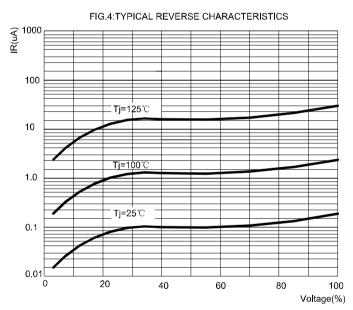
Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

## **Typical Characteristics**

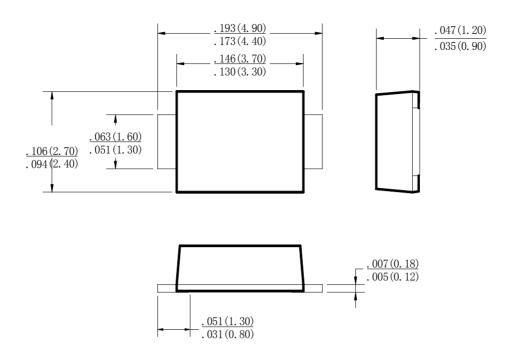






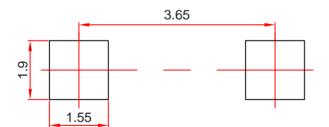


### **SMAF Package Outline Dimensions**



Dimensions in inches and (millimeters)

## **SMAF Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### NOTICE

JSCJ reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

# **Reel Taping Specifications For Surface Mount Devices-SMAF**

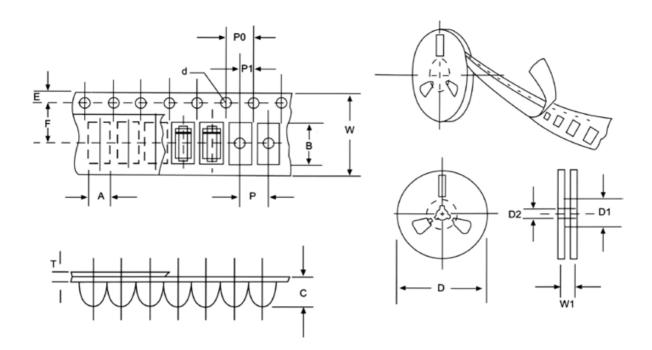


FIG: CONFIGURATION OF SURFACE MOUNTED DEVICES TAPING

ITEM	SYMBOL	SMAF mm(inch)
Carrier width	А	2.83+0.1(0.112+0.004)
Carrier length	В	4.90+0.1(0.193+0.004)
Carrier depth	С	1.45+0.1(0.057+0.004)
Sprocket hole	d	1.55+0.05(0.061+0.002)
Reel outside diameter	D	178+2.0(7.0+0.079)
Reel inner diameter	D1	54±1.0(2.13±0.039)
Feed hole diameter	D2	13+0.5(0.512+0.020)
Strocket hole position	Е	1.75+0.1(0.069+0.004)
Punch hole position	F	5.5+0.05(0.217+0.002)
Punch hole pitch	Р	4.0+0.1(0.157+0.004)
Sprocket hole pitch	P0	4.0+0.1(0.157+0.004)
Embossment center	P1	2.0+0.1(0.079+0.004)
Totall tape thickness	Т	0.23-0.29(0.009-0.011)
Tape width	W	12.0+0.1(0.472+0.004)
Reel width	W1	16.8+2.0(0.661+0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.

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